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Attorney's Docket No. 5308-157IP2

PATENT

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Das et al.

Confirmation No.: 3570

Serial No.: 10/045,542

Group Art Unit: 1762

Filed: October 26, 2001

Examiner: Michael. E. Barr

For: METHOD OF FABRICATING AN OXIDE LAYER ON A SILICON
CARBIDE LAYER UTILIZING AN ANNEAL IN A HYDROGEN
ENVIRONMENT

Date: January 20, 2004

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT UNDER 37

C.F.R. § 1.97(b)

Sir:

Attached is a list of documents on form PTO-1449 together with copies of each identified document. This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(c), before final Office Action or Allowance, whichever is earlier.

Please find attached a check in the amount of \$180.00 for the fee specified in 37 C.F.R. § 1.17(p). The Commissioner is authorized to charge any additional fee or credit any refund to Deposit Account No. 50-0220.

Respectfully submitted,

Elizabeth A. Stanek
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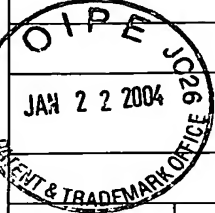
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FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office				Attorney Docket Number 5308-1571P2		Serial No. 10/045,542	
LIST OF DOCUMENTS CITED BY APPLICANT							
(Use several sheets if necessary)							
				Applicants: Das et al.			
				Filing Date: October 26, 2001		Group: 1762	
U. S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
	1	5,479,316	12/26/95	Smrtic et al.	361	322	
	2	5,739,564	04/14/98	Kosa et al.	257	298	
	3	6,228,720	05/08/01	Kitabatake et al.	438	268	
	4	6,239,463	05/29/01	Williams et al.	257	328	
	5	6,316,791	11/13/01	Schorner et al.	257	77	
	6	6,593,620	07/15/03	Hshieh et al.	257	335	
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation Yes No
	7	WO 98/02924	01/22/98	PCT			
	8	WO 00/13236	03/09/00	PCT			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
	9	Dimitrijevic et al., "Nitridation of Silicon-Dioxide Films Grown on 6H Silicon Carbide", <i>IEEE Electronic Device Letters</i> , Vol. 18, No. 5, May 05, 1997, pp. 175-177.					
	10	De Mao et al., "Thermal Oxidation of SiC in N ₂ O", <i>J. Electrochem. Soc.</i> , Vol. 141, 1994, pp. L150-L152.					
	11	Ryu et al., Article and Presentation: "27 mΩ-cm ² , 1.6 kV Power DiMOSFETs in 4H-SiC," <i>Proceedings of the 14 International Symposium on Power Semiconductor Devices & ICs 2002</i> , June 4-7, 2002, Santa Fe, NM.					

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